Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 3 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	55	V
V_{GS}	gate-source voltage			-10	-	10	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	210	mA
		V _{GS} = 4.5 V; T _{sp} = 25 °C		-	-	335	mA
Static charac	cteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_{D} = 200 mA; T_{j} = 25 °C		-	2.3	4	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
BSH111BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
BSH111BK	%4T

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	55	V
V_{GS}	gate-source voltage			-10	10	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	210	mA
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	130	mA
		V_{GS} = 4.5 V; T_{sp} = 25 °C		-	335	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	0.85	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	302	mW
			[1]	-	364	mW
		T _{sp} = 25 °C		-	1449	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode	,				
Is	source current	T _{amb} = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

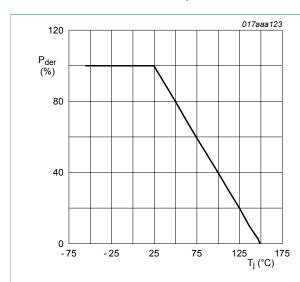


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

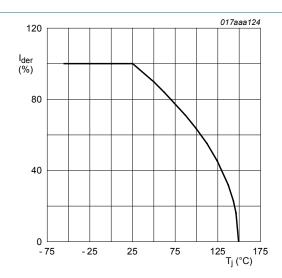


Fig. 2. Normalized continuous drain current as a function of junction temperature

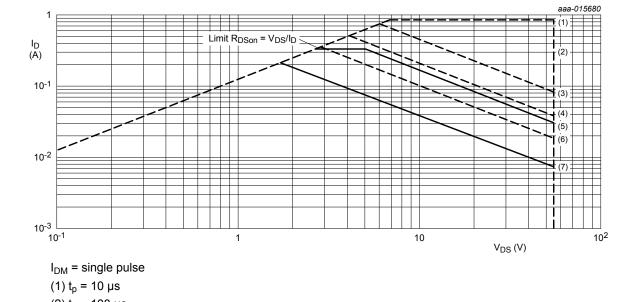
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

BSH111BK

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(2) $t_p = 100 \mu s$

(3) $t_p = 1 \text{ ms}$

(4) $t_p = 10 \text{ ms}$

(5) DC; T_{sp} = 25 °C

(6) $t_p = 100 \text{ ms}$

(7) DC; $T_{amb} = 25 \, ^{\circ}\text{C}$; drain mounting pad 1 cm²

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	_	[1]	-	351	404	K/W
			[2]	-	271	311	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

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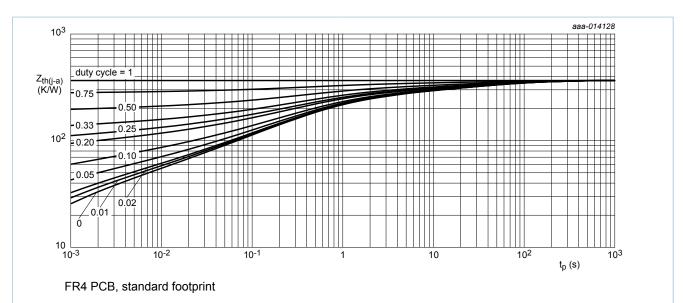


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

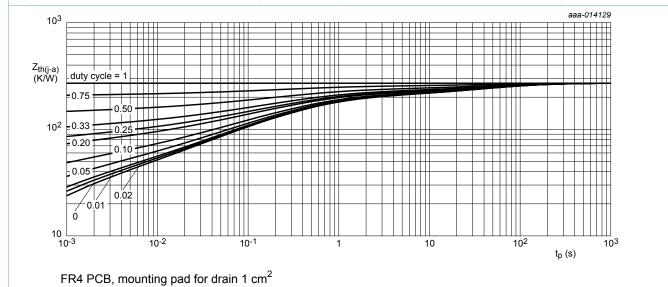


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	55	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.6	1	1.3	V
I _{DSS}	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.3	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 200 mA; T _j = 25 °C	-	2.3	4	Ω
	resistance	V _{GS} = 4.5 V; I _D = 200 mA; T _j = 150 °C	-	4.7	8.1	Ω
		V_{GS} = 2.5 V; I_D = 75 mA; T_j = 25 °C	-	2.7	5	Ω
		V_{GS} = 1.8 V; I_D = 30 mA; T_j = 25 °C	-	4.8	-	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	0.64	-	S
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I_{D} = 200 mA; V_{GS} = 4.5 V;	-	0.5	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.08	-	nC
Q_{GD}	gate-drain charge		-	0.16	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	19.1	30	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.7	10	pF
C _{rss}	reverse transfer capacitance		-	1.5	7	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 200 mA; V _{GS} = 4.5 V;	-	8.3	12	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	8.4	-	ns
t _{d(off)}	turn-off delay time		-	12.6	16	ns
t _f	fall time		-	4.8	-	ns
Source-dra	ain diode		l I		1	
V_{SD}	source-drain voltage	$I_S = 200 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	0.86	1.2	V

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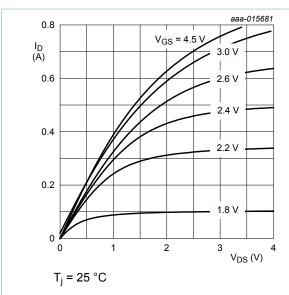
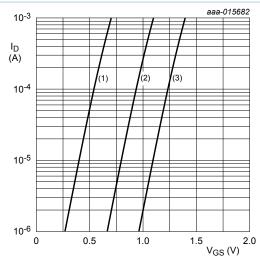


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}C; \, V_{DS} = 5 \,^{\circ}V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

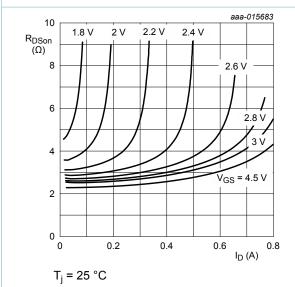
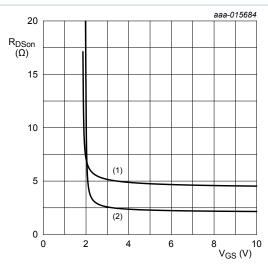


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



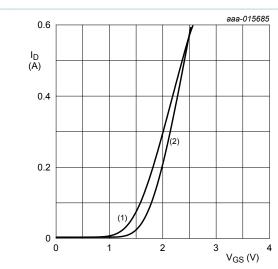
 $I_D = 0.2 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

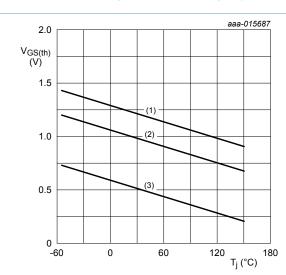
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 $V_{DS} > I_D \times R_{DSon}$ (1) $T_i = 25 \, ^{\circ}C$

(2) $T_i = 150 \, ^{\circ}\text{C}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

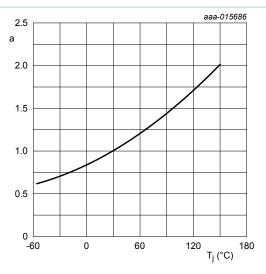
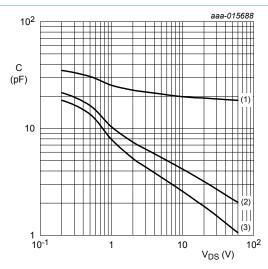


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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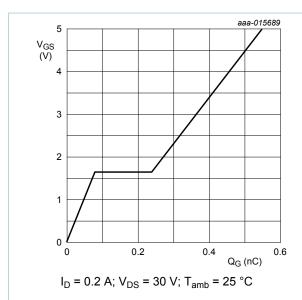


Fig. 14. Gate-source voltage as a function of gate charge; typical values

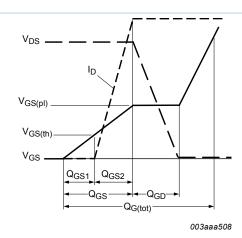
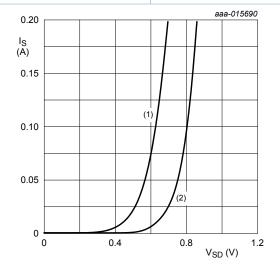


Fig. 15. MOSFET transistor: Gate charge waveform definitions

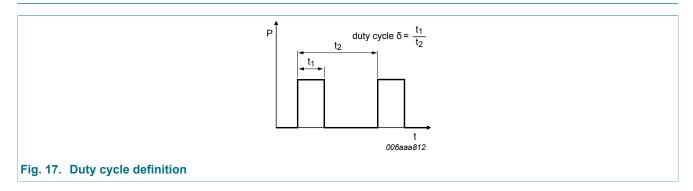


 $V_{GS} = 0 V$ (1) $T_j = 150 °C$ (2) $T_i = 25 °C$

Fig. 16. Source current as a function of source-drain voltage; typical values

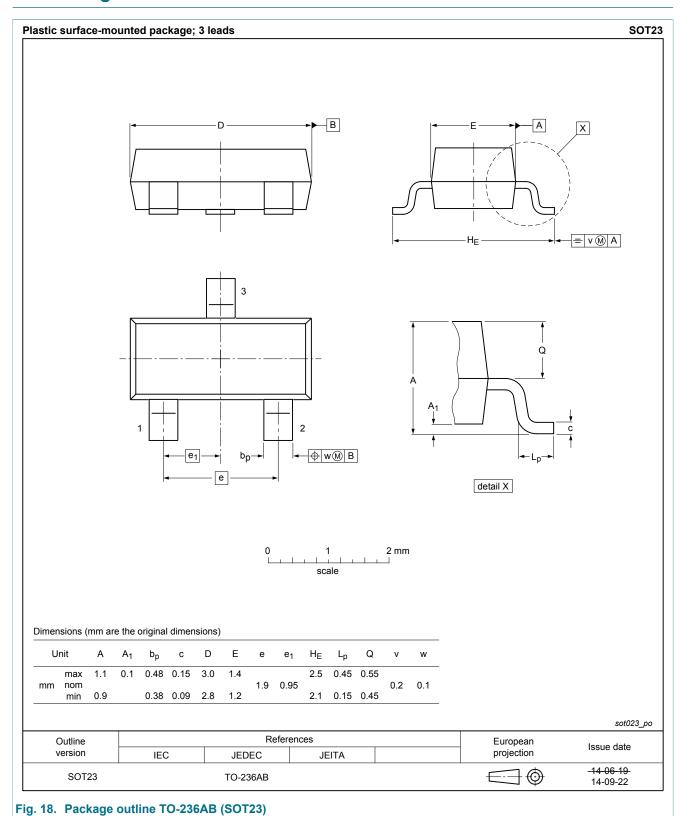
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11. Test information



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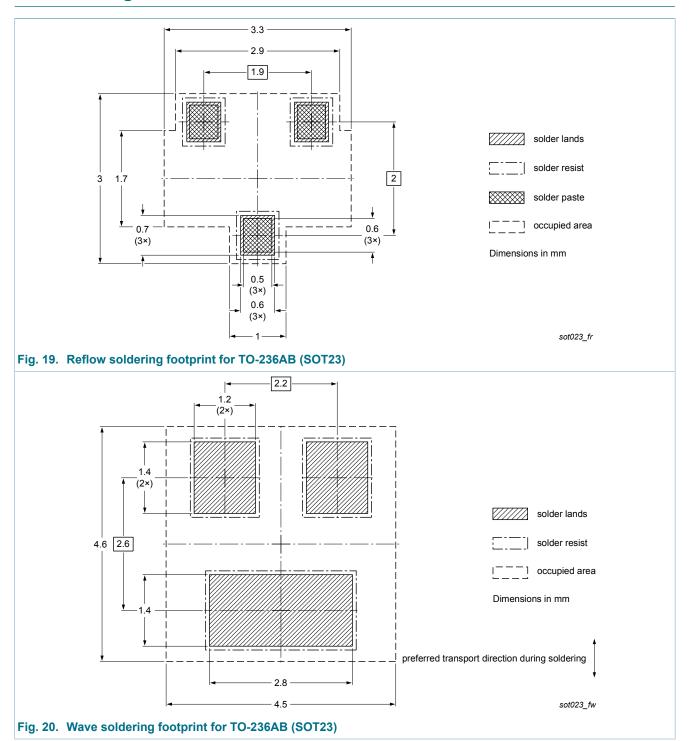
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSH111BK v.1	20141126	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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